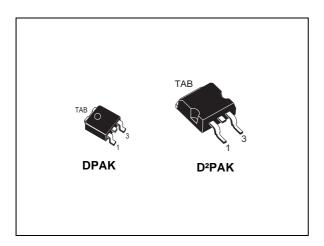


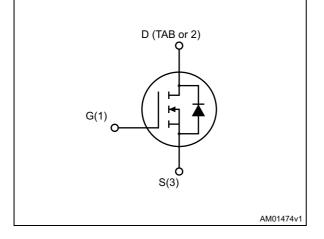
# STB120N4F6, STD120N4F6

Datasheet - production data

# Automotive-grade N-channel 40 V, 3.5 mΩ typ., 80 A STripFET<sup>™</sup> F6 Power MOSFETs in DPAK and D<sup>2</sup>PAK packages



#### Figure 1. Internal schematic diagram



#### Features

| Order codes | $V_{DS}$ | R <sub>DS(on)</sub> max. | ۱ <sub>D</sub> |
|-------------|----------|--------------------------|----------------|
| STB120N4F6  | 40 V     | $4 \text{ m}\Omega$      | 80 A           |
| STD120N4F6  | 40 V     | $4 \text{ m}\Omega$      | 80 A           |

- Designed for automotive applications and AEC-Q101 qualified
- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

## Application

Switching applications

## Description

These devices are N-channel Power MOSFETs developed using the 6<sup>th</sup> generation of STripFET<sup>TM</sup> DeepGATE<sup>TM</sup> technology, with a new gate structure. The resulting Power MOSFETs exhibits the lowest R<sub>DS(on)</sub> in all packages.

#### Table 1. Device summary

| Order codes | Marking   | Package | Packaging     |
|-------------|-----------|---------|---------------|
| STB120N4F6  | 120N4F6   | D²PAK   | Tape and reel |
| STD120N4F6  | 1201141-0 | DPAK    | Tape and Teel |

## Contents

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# 1 Electrical ratings

| Symbol                         | Parameter   | Value      | Unit |
|--------------------------------|---|------------|------|
| $V_{DS}$                       | Drain-source voltage                                  | 40         | V    |
| V <sub>GS</sub>                | Gate-source voltage                                   | ± 20       | V    |
| I <sub>D</sub> <sup>(1)</sup>  | Drain current (continuous) at T <sub>C</sub> = 25 °C  | 80         | А    |
| I <sub>D</sub> <sup>(1)</sup>  | Drain current (continuous) at T <sub>C</sub> = 100 °C | 80         | А    |
| I <sub>DM</sub> <sup>(2)</sup> | Drain current (pulsed)                                | 320        | А    |
| P <sub>TOT</sub>               | Total dissipation at $T_{C} = 25 \text{ °C}$          | 110        | W    |
| T <sub>stg</sub>               | Storage temperature                                   | -55 to 175 | °C   |
| Тj                             | Operating junction temperature                        | -33 10 173 | 0    |

#### Table 2. Absolute maximum ratings

1. Current limited by package

2. Pulse width limited by safe operating area

#### Table 3. Thermal resistance

| Va   | lue                | Unit |
|------|--------------------|------|
| DPAK | D <sup>2</sup> PAK | Onic |
| 1.   | 36                 | °C/W |
| 50   | 35                 | °C/W |
|      | 1.                 | 1.36 |

1. When mounted on 1 inch<sup>2</sup> 2 oz. Cu board.

#### Table 4. Thermal resistance

| Symbol Parameter Value         |   |     |    |  |
|--------------------------------|---|-----|----|--|
| I <sub>AR</sub> <sup>(1)</sup> | Avalanche current, repetitive or not-repetitive | 40  | А  |  |
| E <sub>AS</sub> <sup>(2)</sup> | Single pulse avalanche energy                   | 394 | mJ |  |

1. Pulse width limited by Tj max

2. Starting Tj = 25 °C,  $I_D$  = 40 A,  $V_{DD}$  = 25 V



## 2 Electrical characteristics

(T<sub>CASE</sub> = 25 °C unless otherwise specified)

| Symbol               | Parameter  | Test conditions   | Min. | Тур. | Max.    | Unit     |
|----------------------|--|---|------|------|---------|----------|
| V <sub>(BR)DSS</sub> | Drain-source breakdown<br>Voltage                        | $I_{D} = 250 \ \mu A, \ V_{GS} = 0$                           | 40   |      |         | V        |
| I <sub>DSS</sub>     | Zero gate voltage drain<br>current (V <sub>GS</sub> = 0) | V <sub>DS</sub> = 20 V<br>V <sub>DS</sub> = 20 V, Tc = 125 °C |      |      | 1<br>10 | μΑ<br>μΑ |
| I <sub>GSS</sub>     | Gate body leakage current<br>(V <sub>DS</sub> = 0)       | V <sub>GS</sub> = ± 20 V                                      |      |      | ±100    | nA       |
| V <sub>GS(th)</sub>  | Gate threshold voltage                                   | $V_{DS} = V_{GS}, I_D = 250 \ \mu A$                          | 2    |      | 4       | V        |
| R <sub>DS(on)</sub>  | Static drain-source on resistance                        | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A                 |      | 3.5  | 4.0     | mΩ       |

### Table 5. Static

#### Table 6. Dynamic

| Symbol           | Parameter                       | Test conditions                               | Min | Тур. | Max. | Unit |
|------------------|---------------------------------|---|-----|------|------|------|
| C <sub>iss</sub> | Input capacitance               |   | -   | 3850 | -    | pF   |
| C <sub>oss</sub> | Output capacitance              | V <sub>DS</sub> = 25 V, f=1 MHz,              | -   | 650  | -    | pF   |
| C <sub>rss</sub> | Reverse transfer<br>capacitance | V <sub>GS</sub> = 0 V                         | -   | 350  | -    | pF   |
| Qg               | Total gate charge               | V <sub>DD</sub> = 20 V, I <sub>D</sub> = 80 A | -   | 65   | -    | nC   |
| Q <sub>gs</sub>  | Gate-source charge              | V <sub>GS</sub> = 10 V                        | -   | 20   | -    | nC   |
| Q <sub>gd</sub>  | Gate-drain charge               | (see Figure 14)                               | -   | 16   | -    | nC   |
| R <sub>G</sub>   | Intrinsic gate resistance       | f = 1 MHz open drain                          | -   | 1.5  | -    | Ω    |

#### Table 7. Switching on/off (inductive load)

| Symbol              | Parameter           | Test conditions   | Min. | Тур. | Max. | Unit |
|---------------------|---------------------|---|------|------|------|------|
| t <sub>d(on)</sub>  | Turn-on delay time  |   | -    | 20   | -    | ns   |
| t <sub>r</sub>      | Rise time           | $V_{DD} = 20 \text{ V}, \text{ I}_{D} = 40 \text{ A},$<br>$R_{G} = 4.7 \Omega, V_{GS} = 10 \text{ V}$ | -    | 70   | -    | ns   |
| t <sub>d(off)</sub> | Turn-off delay time | (see Figure 15)   | -    | 40   | -    | ns   |
| t <sub>f</sub>      | Fall time           | , j   | -    | 20   | -    | ns   |



| Symbol   | Parameter   | Test conditions                             | Min. | Тур. | Max.      | Unit   |
|--|---|---|------|------|-----------|--------|
| I <sub>SD</sub><br>I <sub>SDM</sub> <sup>(1)</sup> | Source-drain current<br>Source-drain current (pulsed) |   | -    |      | 80<br>320 | A<br>A |
| $V_{SD}^{(2)}$                                     | Forward on voltage                                    | I <sub>SD</sub> = 40 A, V <sub>GS</sub> = 0 | -    |      | 1.1       | V      |
| t <sub>rr</sub>                                    | Reverse recovery time                                 | I <sub>SD</sub> = 80 A,                     | -    | 40   |           | ns     |
| Q <sub>rr</sub>                                    | Reverse recovery charge                               | $di/dt = 100 A/\mu s,$                      | -    | 56   |           | nC     |
| I <sub>RRM</sub>                                   | Reverse recovery current                              | V <sub>DD</sub> = 30 V<br>(see Figure 17)   | -    | 2.8  |           | А      |

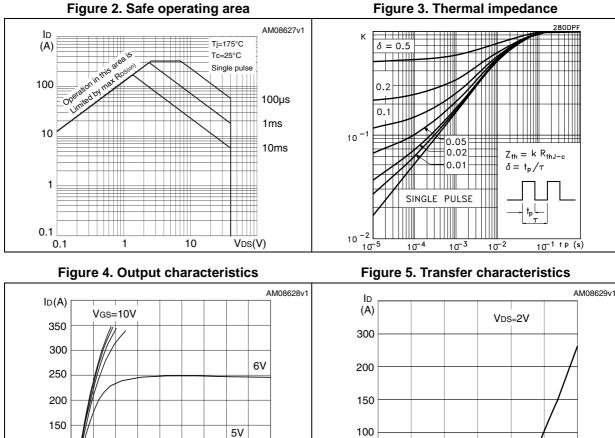
Table 8. Source drain diode

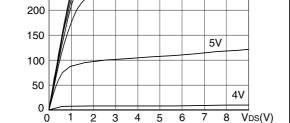
1. Pulse width limited by safe operating area

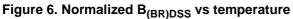
2. Pulsed: pulse duration =  $300 \ \mu$ s, duty cycle 1.5%



#### **Electrical characteristics (curves)** 2.1







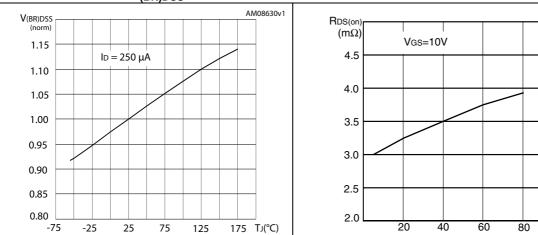


Figure 7. Static drain-source on resistance

3

4

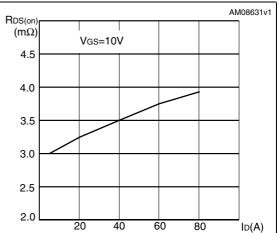
5

2

1

50

0



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VGS(V)

#### Figure 8. Gate charge vs gate-source voltage

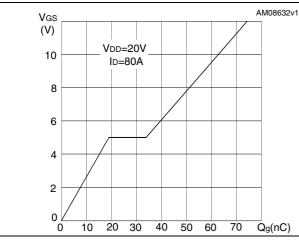


Figure 10. Normalized gate threshold voltage vs temperature

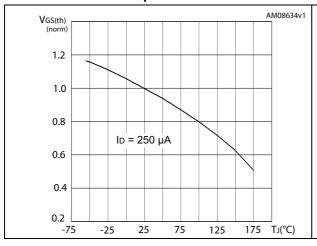


Figure 12. Source-drain diode forward characteristics

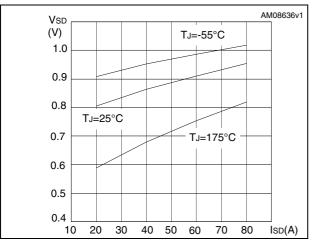




Figure 9. Capacitance variations

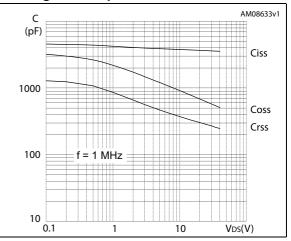
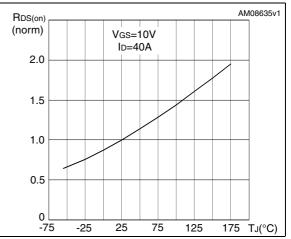


Figure 11. Normalized on resistance vs temperature



## 3 Test circuits

Figure 13. Switching times test circuit for resistive load

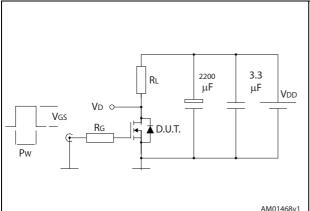
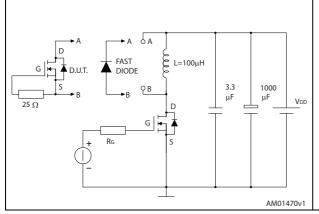


Figure 15. Test circuit for inductive load switching and diode recovery times





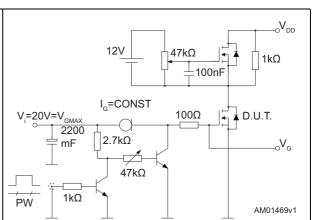
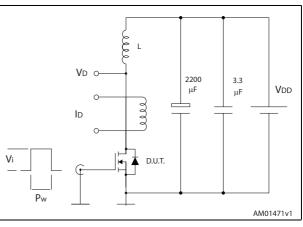
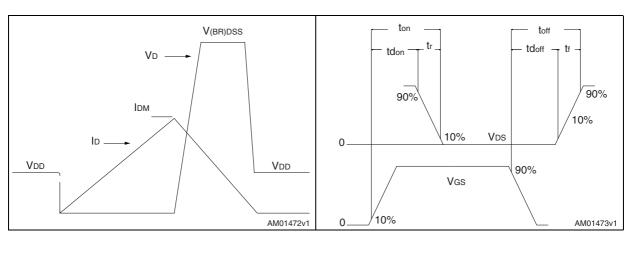


Figure 14. Gate charge test circuit









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## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and products status are available at: <u>www.st.com</u>. ECOPACK is an ST trademark.

## 4.1 D<sup>2</sup>PAK (TO-263) type A package information

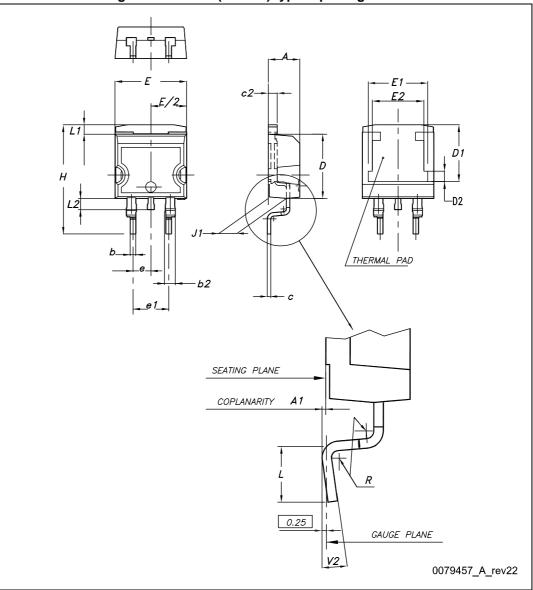


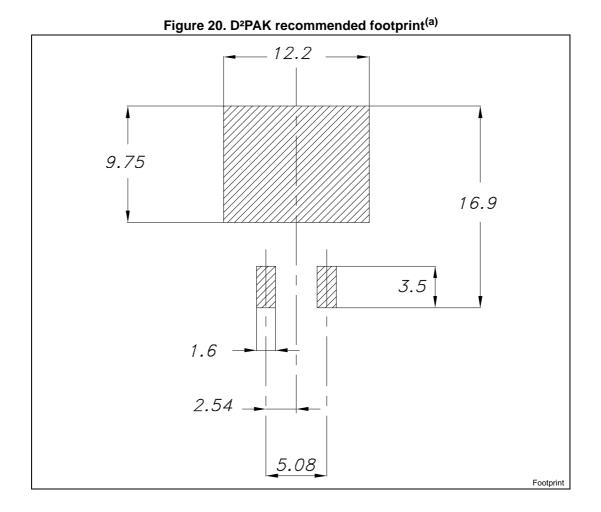
Figure 19. D<sup>2</sup>PAK (TO-263) type A package outline



| Dim  |      | mm   |       |
|------|------|------|-------|
| Dim. | Min. | Тур. | Max.  |
| А    | 4.40 |      | 4.60  |
| A1   | 0.03 |      | 0.23  |
| b    | 0.70 |      | 0.93  |
| b2   | 1.14 |      | 1.70  |
| С    | 0.45 |      | 0.60  |
| c2   | 1.23 |      | 1.36  |
| D    | 8.95 |      | 9.35  |
| D1   | 7.50 | 7.75 | 8.00  |
| D2   | 1.10 | 1.30 | 1.50  |
| E    | 10   |      | 10.40 |
| E1   | 8.50 | 8.70 | 8.90  |
| E2   | 6.85 | 7.05 | 7.25  |
| е    |      | 2.54 |       |
| e1   | 4.88 |      | 5.28  |
| Н    | 15   |      | 15.85 |
| J1   | 2.49 |      | 2.69  |
| L    | 2.29 |      | 2.79  |
| L1   | 1.27 |      | 1.40  |
| L2   | 1.30 |      | 1.75  |
| R    |      | 0.4  |       |
| V2   | 0°   |      | 8°    |

Table 9. D<sup>2</sup>PAK (TO-263) type A mechanical data

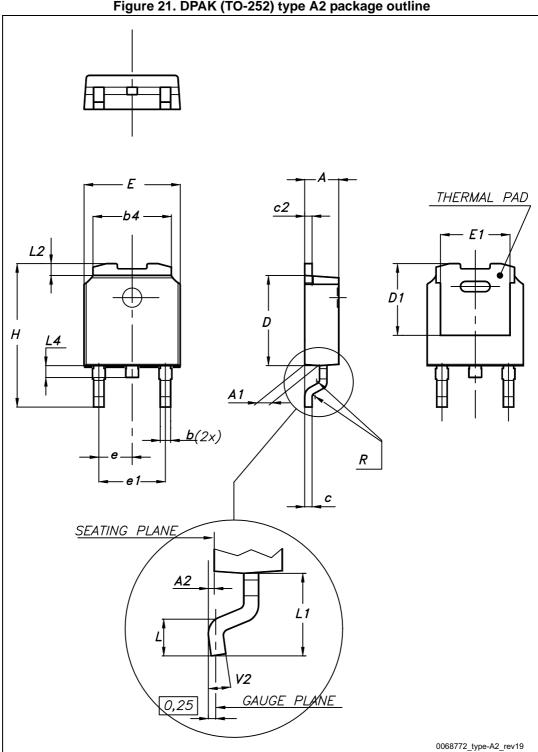




a. All dimension are in millimeters



#### DPAK (TO-252) type A2 package information 4.2





| Dim    |      | mm   |       |  |
|--------|------|------|-------|--|
| Dim. — | Min. | Тур. | Max.  |  |
| А      | 2.20 |      | 2.40  |  |
| A1     | 0.90 |      | 1.10  |  |
| A2     | 0.03 |      | 0.23  |  |
| b      | 0.64 |      | 0.90  |  |
| b4     | 5.20 |      | 5.40  |  |
| С      | 0.45 |      | 0.60  |  |
| c2     | 0.48 |      | 0.60  |  |
| D      | 6.00 |      | 6.20  |  |
| D1     | 4.95 | 5.10 | 5.25  |  |
| E      | 6.40 |      | 6.60  |  |
| E1     | 5.10 | 5.20 | 5.30  |  |
| е      | 2.16 | 2.28 | 2.40  |  |
| e1     | 4.40 |      | 4.60  |  |
| Н      | 9.35 |      | 10.10 |  |
| L      | 1.00 |      | 1.50  |  |
| L1     | 2.60 | 2.80 | 3.00  |  |
| L2     | 0.65 | 0.80 | 0.95  |  |
| L4     | 0.60 |      | 1.00  |  |
| R      |      | 0.20 |       |  |
| V2     | 0°   |      | 8°    |  |

Table 10. DPAK (TO-252) type A2 mechanical data



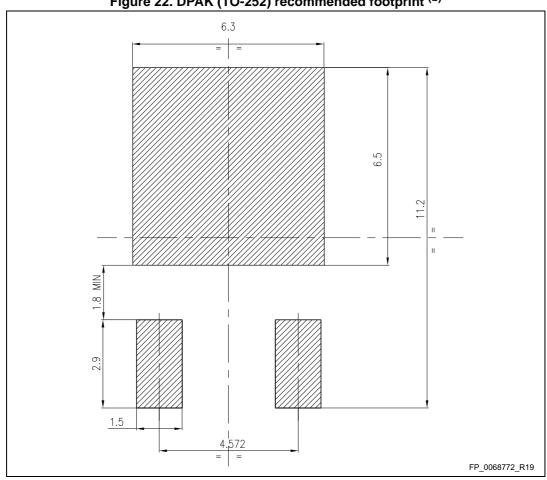
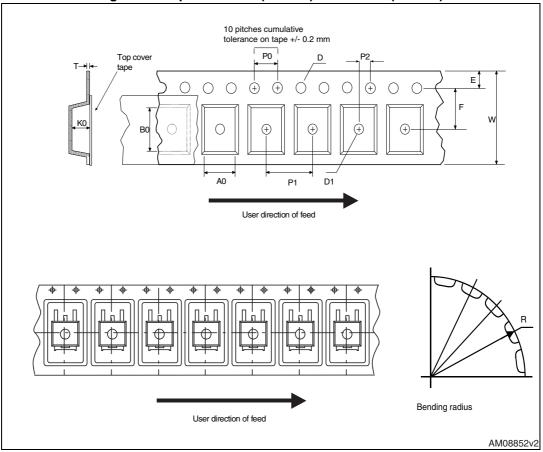


Figure 22. DPAK (TO-252) recommended footprint <sup>(b)</sup>

b. All dimensions are in millimeters

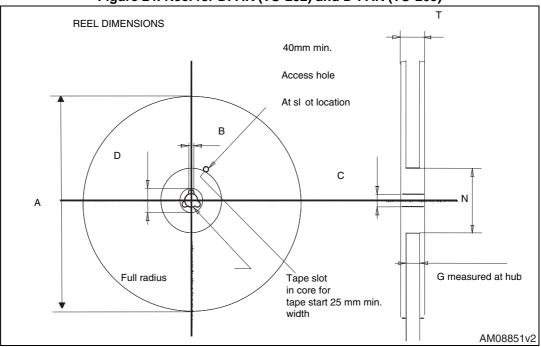


## 5 Packaging mechanical data



#### Figure 23. Tape for DPAK (TO-252) and D<sup>2</sup>PAK (TO-263)





#### Figure 24. Reel for DPAK (TO-252) and D<sup>2</sup>PAK (TO-263)

### Table 11. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

| Таре |      |      | Reel          |      |      |
|------|------|------|---------------|------|------|
| Dim. | mm   |      | Dim           | mm   |      |
|      | Min. | Max. | Dim.          | Min. | Max. |
| A0   | 10.5 | 10.7 | А             |      | 330  |
| B0   | 15.7 | 15.9 | В             | 1.5  |      |
| D    | 1.5  | 1.6  | С             | 12.8 | 13.2 |
| D1   | 1.59 | 1.61 | D             | 20.2 |      |
| E    | 1.65 | 1.85 | G             | 24.4 | 26.4 |
| F    | 11.4 | 11.6 | N             | 100  |      |
| K0   | 4.8  | 5.0  | Т             |      | 30.4 |
| P0   | 3.9  | 4.1  |               |      |      |
| P1   | 11.9 | 12.1 | Base qty 1000 |      |      |
| P2   | 1.9  | 2.1  | Bulk qty 1000 |      |      |
| R    | 50   |      |               |      |      |
| Т    | 0.25 | 0.35 |               |      |      |
| W    | 23.7 | 24.3 |               |      |      |



|      | Таре |      |      | Reel      |      |  |
|------|------|------|------|-----------|------|--|
| Dim. | mm   |      | Dim. | mm        |      |  |
|      | Min. | Max. | Dim. | Min.      | Max. |  |
| A0   | 6.8  | 7    | А    |           | 330  |  |
| B0   | 10.4 | 10.6 | В    | 1.5       |      |  |
| B1   |      | 12.1 | С    | 12.8      | 13.2 |  |
| D    | 1.5  | 1.6  | D    | 20.2      |      |  |
| D1   | 1.5  |      | G    | 16.4      | 18.4 |  |
| E    | 1.65 | 1.85 | Ν    | 50        |      |  |
| F    | 7.4  | 7.6  | Т    |           | 22.4 |  |
| K0   | 2.55 | 2.75 |      |           |      |  |
| P0   | 3.9  | 4.1  |      | Base qty. | 2500 |  |
| P1   | 7.9  | 8.1  |      | Bulk qty. | 2500 |  |
| P2   | 1.9  | 2.1  |      |           |      |  |
| R    | 40   |      |      |           |      |  |
| Т    | 0.25 | 0.35 |      |           |      |  |
| W    | 15.7 | 16.3 |      |           |      |  |

Table 12. DPAK (TO-252) tape and reel mechanical data



# 6 Revision history

| Date        | Revision | Changes   |  |  |  |  |
|-------------|----------|---|--|--|--|--|
| 09-Feb-2010 | 1        | First release   |  |  |  |  |
| 29-Oct-2010 | 2        | Document status promoted from preliminary data to datasheet.                                      |  |  |  |  |
| 11-Nov-2010 | 3        | Corrected R <sub>DS(on)</sub> value in <i>Table 5: Static</i> .                                   |  |  |  |  |
| 13-May-2011 | 4        | Removed package and mechanical data: TO-220   |  |  |  |  |
| 17-May-2011 | 5        | Description in cover page has been updated.   |  |  |  |  |
| 23-Sep-2015 | 6        | Updated title, features and description in cover page.<br>Updated Section 4: Package information. |  |  |  |  |

#### Table 13. Document revision history



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